

Form PTO-1449 (modified)

Atty. Docket No.:

11762.0284.CNUS01

Serial No.:

09/923,058

Applicants:

David S. Becker, et al.

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FEB 12 2003  
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List of Patents and Publications for Applicant's  
INFORMATION DISCLOSURE STATEMENT  
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Filing Date:

August 6, 2001

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1763

U.S. Patent Documents

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Foreign Patent Documents

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Other Art

TC 1700  
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U.S. Patent Documents							
Exam. Init.	Ref. Des.	Document Number	Date	Name	Class	Sub Class	Filing Date of App.
gpg	A1	4,283,249 ✓	08/11/1981	Ephrath, L.M.	156	643	08/17/1979
	A2	4,352,724 ✓	10/5/1982	Sugishima, et al.	204	192	11/19/1980
	A3	4,371,407 ✓	02/01/1983	Kurosawa, K.	148	187	10/28/1981
	A4	4,461,672 ✓	07/24/1984	Musser, M.E.	156	644	11/18/1982
	A5	4,522,681 ✓	06/11/1985	Gorowitz, et al.	156	643	04/23/1984
	A6	4,952,274 ✓	08/28/1990	Abraham, T.	156	643	05/27/1988
	A7	4,966,870 ✓	10/30/1990	Barber, et al.	437	228	08/08/1989
	A8	5,176,790 ✓	01/05/1993	Arleo, et al.	156	643	09/25/1991
	A9	5,200,358 ✓	04/06/1993	Bollinger, et al.	437	180	11/15/1991
	A10	5,244,837 ✓	09/14/1993	Dennison, C.H.	437	195	03/19/1993
	A11	5,290,726 ✓	03/01/1994	Kim, H.S.	437	52	02/18/1992
	A12	5,298,463 ✓	03/29/1994	Sandhu, et al.	437	192	04/16/1992
	A13	5,302,236 ✓	04/12/1994	Tahara, et al.	156	643	10/18/1991
	A14	5,321,211 ✓	06/14/1994	Haslam, et al.	174	262	04/30/1992
	A15	5,338,700 ✓	08/16/1994	Dennison, et al.	437	60	04/14/1993
	A16	5,366,590 ✓	11/22/1994	Kadomura, S.	156	662	03/17/1994
gpg	A17	5,372,969 ✓	12/13/1994	Moslehi, M. M.	437	195	03/03/1992
	A18						

## Foreign Patent Documents

Exam. Init.	Ref. Des.	Document Number	Date	Country	Class	Sub Class	Translation
gpg	B1	JP58053833 ✓	03/30/1983	Japan	156	205	Abstract only
gpg	B2	JP60143633 ✓	07/29/1985	Japan	—	—	—

EXAMINER: George Gouldreau DATE CONSIDERED: 5-031

EXAMINER: INITIAL IF REFERENCE CONSIDERED, WHETHER OR NOT CITATION IS IN CONFORMANCE WITH MPEP609; DRAW LINE THROUGH CITATION IF NOT IN CONFORMANCE AND NOT CONSIDERED. INCLUDE COPY OF THIS FORM WITH NEXT COMMUNICATION TO APPLICANT.

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1763U.S. Patent Documents  
*See Page 1*Foreign Patent Documents  
*See Pages 1-2*Other Art  
*See Pages 2-3*RECEIVED  
FEB 14 2003  
TC 1700**Foreign Patent Documents**

Exam. Init.	Ref. Des.	Document Number	Date	Country	Class	Sub Class	Translation Yes/No
grag	B3	JP02198634V	08/07/1990	Japan	B01J	23/24	Abstract only
	B4	JP03262503V	11/22/1991	Japan	B01D	19/00	Abstract only
	B5	JP04180222V	06/26/1992	Japan	H01L	21/302	Abstract only
	B6	JP04298032V	10/21/1992	Japan	H01L	21/302	Abstract only
grag	B7						

**Other Art (Including Author, Title, Date Pertinent Pages, Etc.)**

Exam. Init.	Ref. Des.	Citation
grag	C1	Vossen, J.L.; Cuomo, J.J., "Glow Discharge Sputter Deposition", in <i>Thin Film Processes</i> , Vossen, J.L.; Kern, W., Eds.; Academic Press, New York: 1978; pp. 11-73. ✓
	C2	Coburn, J.W.; Kay, E., "Some Chemical Aspects of the Fluorocarbon Plasma Etching of Silicon and Its Compounds", <i>IBM J. Res. Develop.</i> 1979, Vol. 23(1); 33-41. ✓
	C3	Toyoda, H.; Komiya, H.; Itakura, H., "Etching Characteristics of SiO <sub>2</sub> in CHF <sub>3</sub> Gas Plasma", <i>J. Electronic Mat.</i> 1980, Vol. 9(3); 569-584. ✓
	C4	Flamm, D.L.; Donnelly, V.M., "The Design of Plasma Etchants", <i>Plasma Chemistry and Plasma Processing</i> 1981, Vol. 1(4); 317-363. ✓
	C5	Kusters, K.H.; Sesselmann, W.; Melzner, H.; Friesel, B., "A Self Aligned Contact Process with Improved Surface Planarization", <i>Journal de Physique</i> 1988, Vol. 49, Colloque C4, Suppl. 9; C4503 - C4506. ✓
	C6	Chang, E.Y.; van Hove, J.M.; Pande, K.P., "A Selective Dry-Etch Technique for GaAs MESFET Gate Recessing", <i>IEEE Trans. Electron. Devices</i> 1988, Vol. 35(10); 1580-1584. ✓
	C7	Nojiri, K.; Iguchi, E.; Kawamura, K.; Kadota, K., "Microwave Plasma Etching of Silicon Dioxide for Half-Micron ULSIs", in <i>Extended Abstracts of the 21<sup>st</sup> Conference on Solid State Devices and Materials</i> , Tokyo, 1989; pp. 153-156. ✓
grag	C8	Grande, W.J.; Johnson, J.E.; Tang, C.L., "Characterization of Etch Rate and Anisotropy in the Temperature-Controlled Chemically Assisted Ion Beam Etching of GaAs", <i>J. Vac. Sci. Technol. B</i> , 1990, Vol. 8(5); 1075-1079. ✓

EXAMINER: George Goudreau

DATE CONSIDERED: 5-03/

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*See Pages 1-2*Other Art  
*See Pages 2-3***Other Art (Including Author, Title, Date Pertinent Pages, Etc.)**

<b>Exam. Init.</b>	<b>Ref. Des.</b>	<b>Citation</b>
OPIF J	C9	Simko, J.P.; Oehrlein, G.S., "Reactive Ion Etching of Silicon and Silicon Dioxide in CF <sub>4</sub> Plasmas Containing H <sub>2</sub> or C <sub>2</sub> F <sub>4</sub> Additives", <i>J. Electrochem. Soc.</i> 1991, Vol. 138 (9); 2748-2752. ✓
J	C10	Marks, J.; Collins, K.; Yang, C.L.; Groechel, D.; Keswick, P.; Cunningham, C.; Carlson, M., "Introduction of a New High Density Plasma Reactor Concept for High Aspect Ratio Oxide Etching", <i>SPIE Vol. 1803 (1992)</i> ; pp. 235-247. ✓
	C11	Sakai, T.; Hayashi, H.; Abe, J.; Horioka, K.; Okano, H., "Examination of Selective Etching and Etching Damage with Mass-Selected Ion Beam", <i>1993 Dry Process Symposium</i> ; 193-198. ✓
	C12	Preliminary Invalidity Contentions regarding Parent Patent 5,286,344, filed in <i>Sandisk Corp. v. Micron Tech., Inc.</i> , Civ. No. CV02-2627CW (N. D. Cal.). ✓
	C13	Preliminary Invalidity Contentions regarding Parent Patent 6,015,760, filed in <i>Sandisk Corp. v. Micron Tech., Inc.</i> , Civ. No. CV02-2627CW (N. D. Cal.). ✓
OPIF J	C14	Preliminary Invalidity Contentions regarding Parent Patent 6,281,978, filed in <i>Sandisk Corp. v. Micron Tech., Inc.</i> , Civ. No. CV02-2627CW (N. D. Cal.). ✓
	C15	

**EXAMINER:** George Goldreich **DATE CONSIDERED:** 5-031

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